

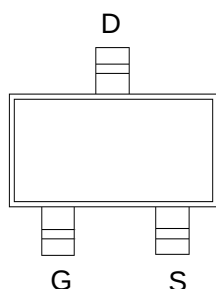
100V/2A N-Channel MOSFET

Features

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

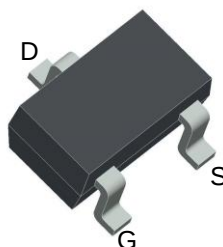
Application

- Consumer electronic power supply
- Motor control
- Synchronous-rectification
- Isolated DC/DC convertor

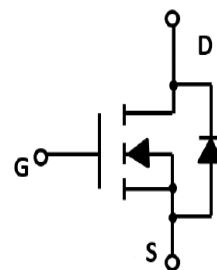


Product Summary

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
100V	630mΩ@10V	2A
	720mΩ@4.5V	



SOT-23-3L top view



Schematic diagram



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 2	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 9.4	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 2	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 1.4	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	85	°C/W

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.7	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =1A	--	250	630	mΩ
		V _{GS} =4.5V, I _D =0.8A	--	350	720	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	--	387	--	pF
C _{OSS}	Output Capacitance		--	31	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	28	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =50V, I _D =2A, V _{GS} =10V	--	9.5	--	nC
Q _{gs}	Gate Source Charge		--	1.8	--	nC
Q _{gd}	Gate Drain Charge		--	1.98	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =50V, I _D =1.3A, V _{GS} =10V, R _G =1Ω	--	4	--	nS
t _r	Turn-on Rise Time		--	18	--	nS
t _{d(off)}	Turn-Off Delay Time		--	13.5	--	nS
t _f	Turn-Off Fall Time		--	28	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=2A,	--	--	1.2	V

Typical Operating Characteristics

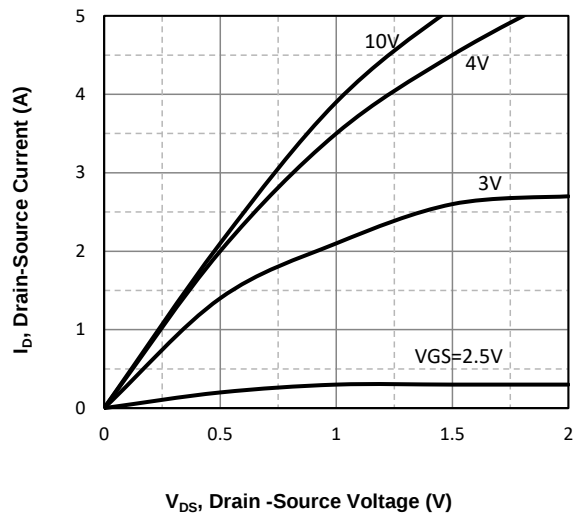


Fig1. Typical Output Characteristics

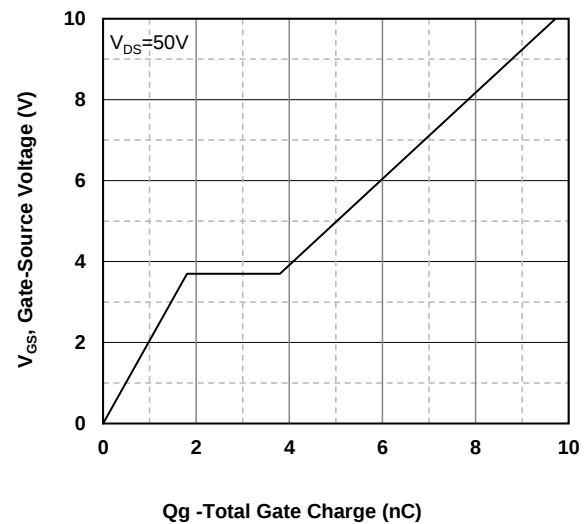


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

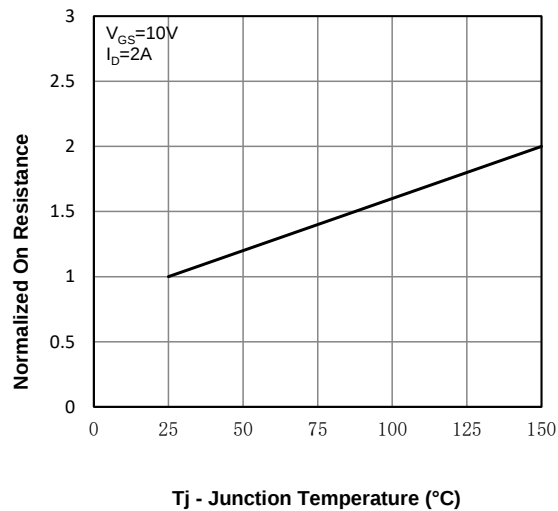


Fig3. Normalized On-Resistance Vs. Temperature

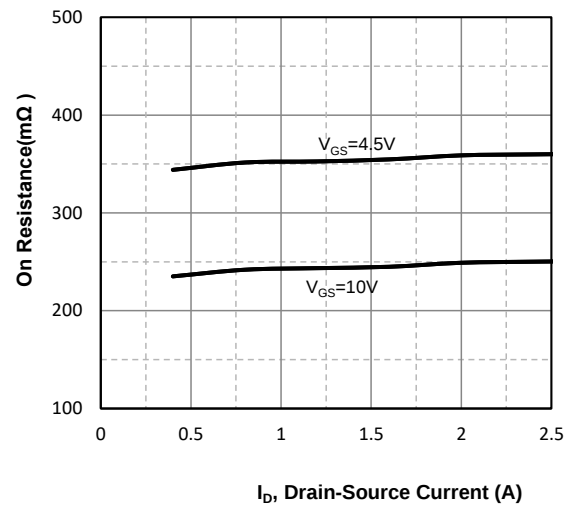


Fig4. On-Resistance Vs. Drain-Source Current

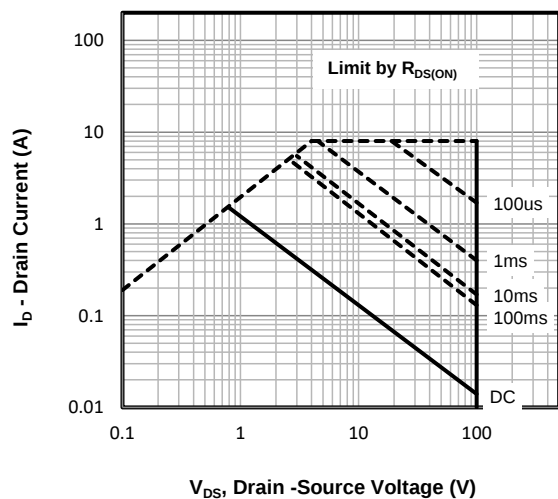


Fig5. Maximum Safe Operating Area

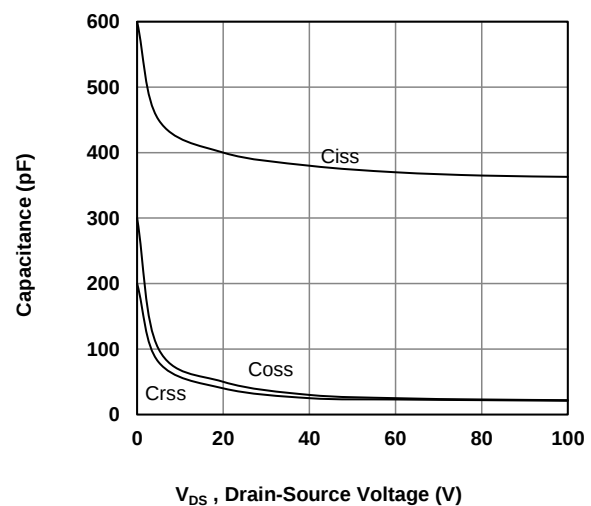
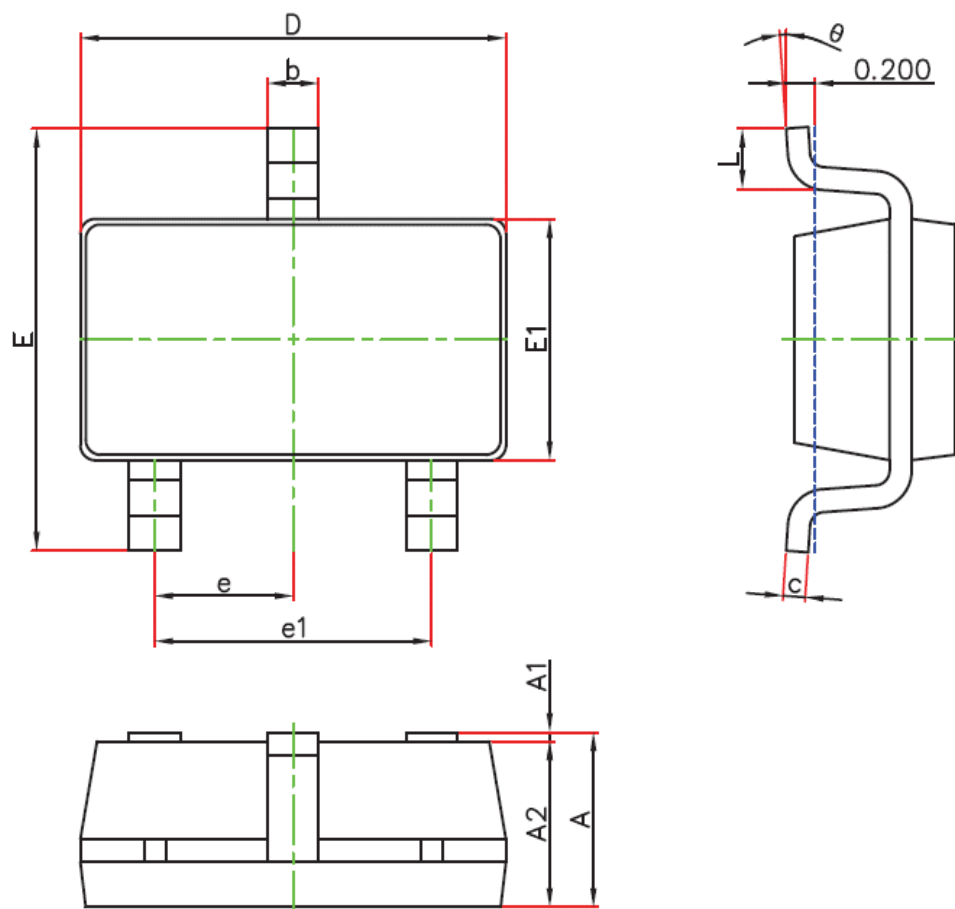


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23-3L Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°